

NPN Silicon Darlington Transistor

- High collector current
- Low collector-emitter saturation voltage
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
SMBTA14/MMBTA14	s1N	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	30	V
Collector-base voltage	V_{CBO}	30	
Emitter-base voltage	V_{EBO}	10	
Collector current	I_C	300	mA
Peak collector current	I_{CM}	500	
Base current	I_B	100	
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 81 \text{ }^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 210	K/W

¹⁾Pb-containing package may be available upon special request

²⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

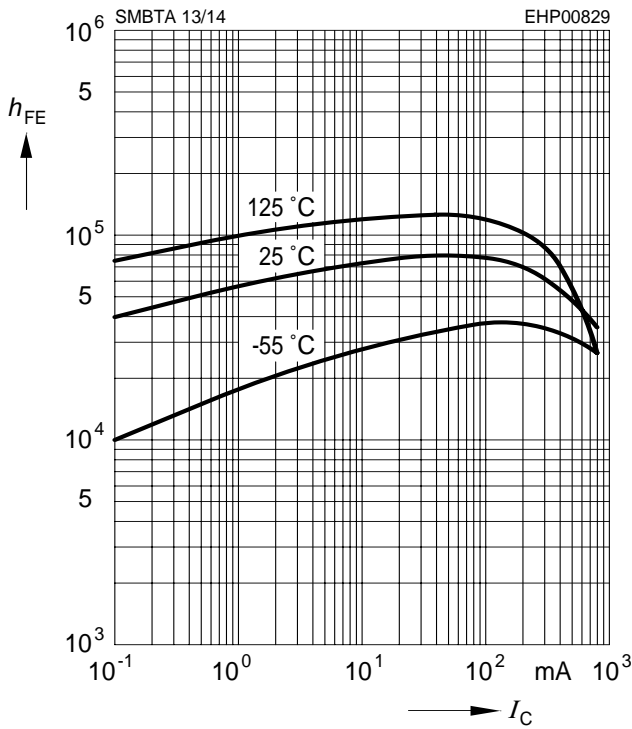
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	30	-	-	V
Collector-emitter breakdown voltage $I_C = 10 \mu\text{A}, V_{BE} = 0$	$V_{(BR)CES}$	30	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	10	-	-	
Collector-base cutoff current $V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	I_{CBO}	-	-	0.1 10	μA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	10000 20000	- -	- -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$	V_{CEsat}	-	-	1.5	V
Base emitter saturation voltage ¹⁾ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$	V_{BEsat}	-	-	2	
AC Characteristics					
Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}, f = 20 \text{ MHz}$	f_T	125	-	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 100 \text{ MHz}$	C_{cb}	-	3	-	pF

¹⁾Pulse test: $t < 300\mu\text{s}; D < 2\%$

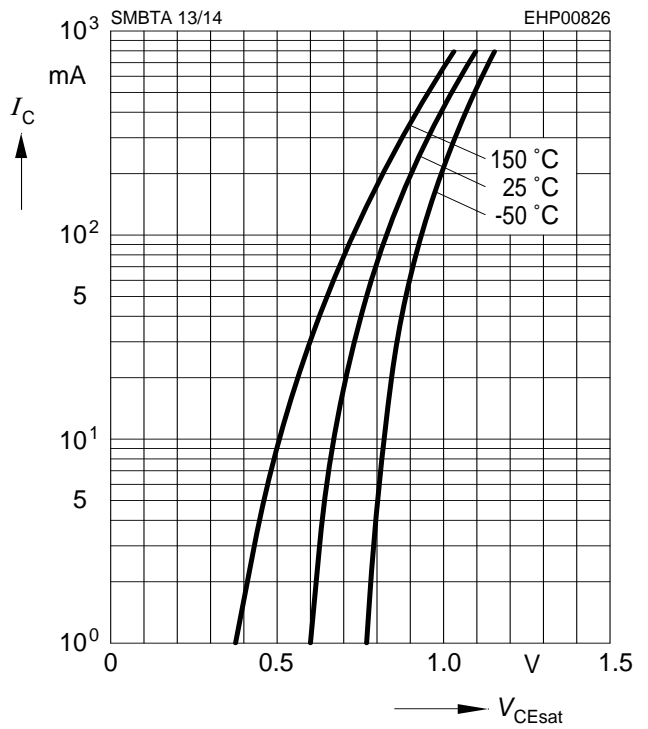
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$



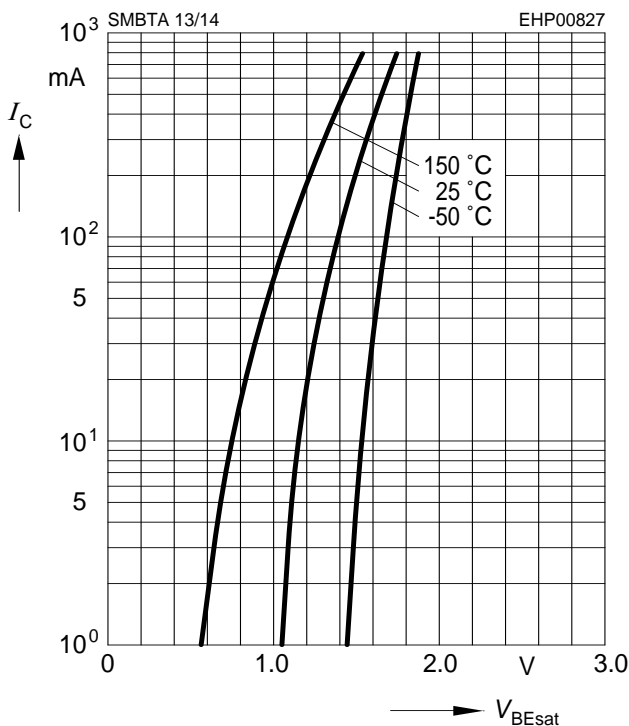
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 1000$



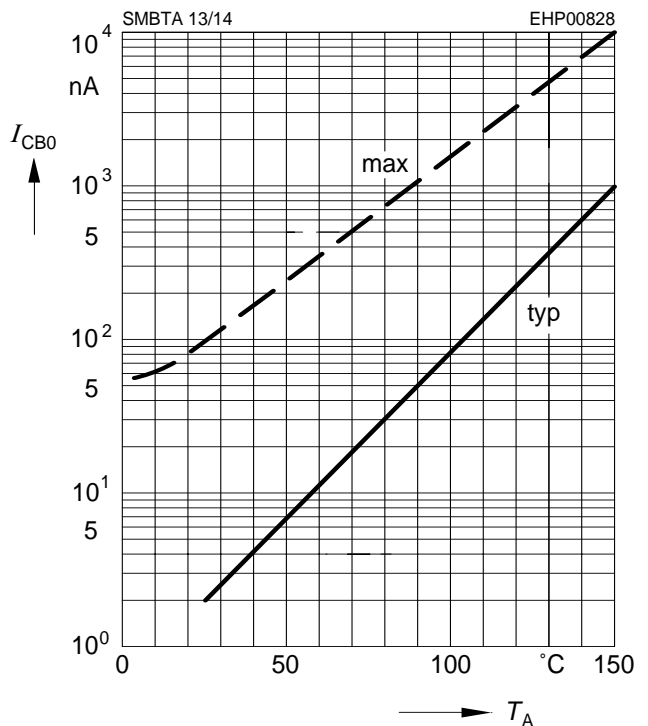
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 1000$



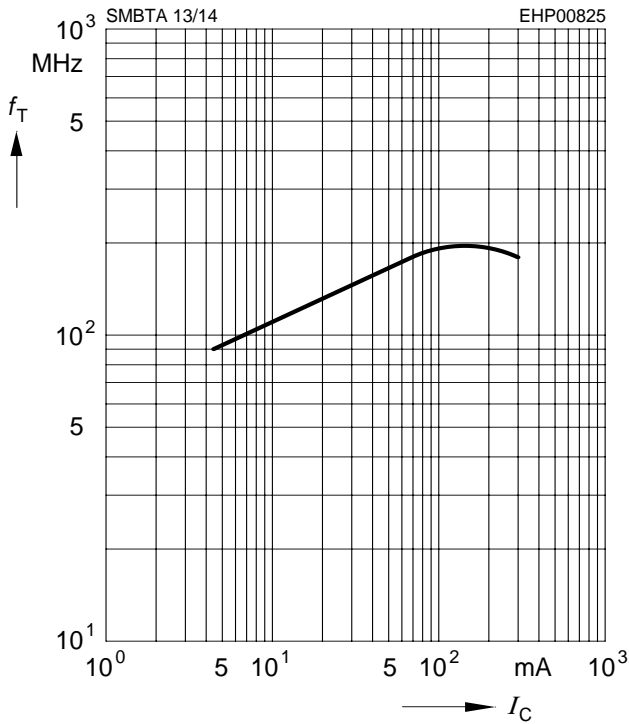
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30\text{ V}$



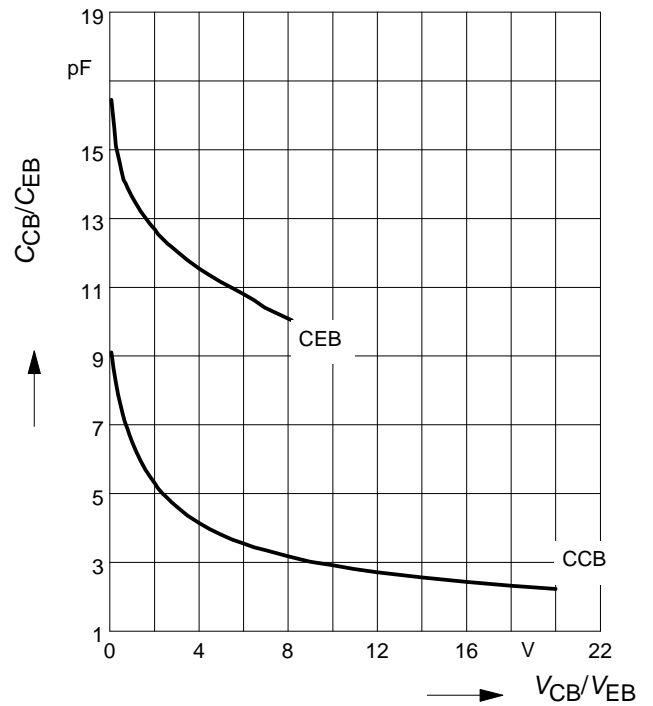
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\text{ V}, f = 200\text{ MHz}$

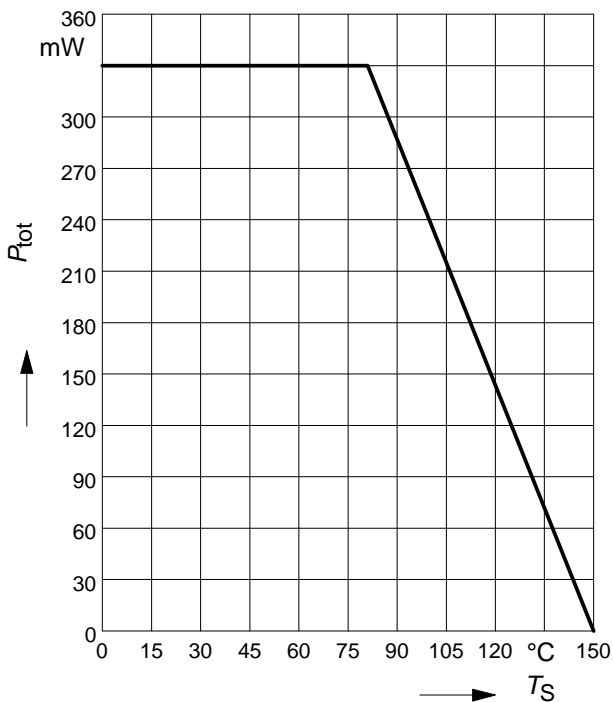


Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$

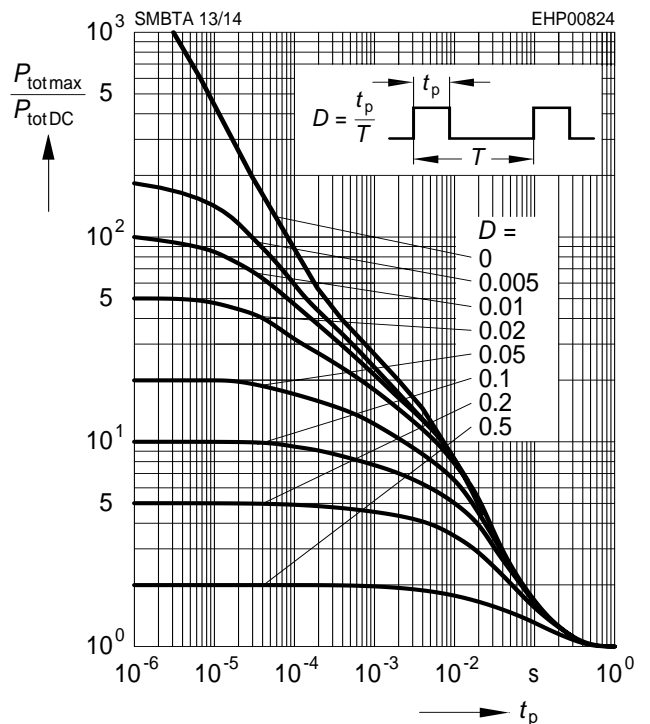


Total power dissipation $P_{tot} = f(T_S)$



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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